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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	104
Number of Gates	14000
Voltage - Supply	3V ~ 3.6V, 4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	176-LQFP
Supplier Device Package	176-TQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a42mx09-1tqg176i

3.3.7 Low Power Mode

42MX devices have been designed with a Low Power Mode. This feature, activated with setting the special LP pin to HIGH for a period longer than 800 ns, is particularly useful for battery-operated systems where battery life is a primary concern. In this mode, the core of the device is turned off and the device consumes minimal power with low standby current. In addition, all input buffers are turned off, and all outputs and bidirectional buffers are tristated. Since the core of the device is turned off, the states of the registers are lost. The device must be re-initialized when exiting Low Power Mode. I/Os can be driven during LP mode, and clock pins should be driven HIGH or LOW and should not float to avoid drawing current. To exit LP mode, the LP pin must be pulled LOW for over 200 µs to allow for charge pumps to power up, and device initialization will begin.

3.4 Power Dissipation

The general power consumption of MX devices is made up of static and dynamic power and can be expressed with the following equation.

3.4.1 General Power Equation

$$P = [ICCstandby + ICCactive]*VCCI + IOL*VOL*N + IOH*(VCCI - VOH)*M$$

EQ 1

where:

- ICCstandby is the current flowing when no inputs or outputs are changing.
- ICCactive is the current flowing due to CMOS switching.
- IOL, IOH are TTL sink/source currents.
- VOL, VOH are TTL level output voltages.
- N equals the number of outputs driving TTL loads to VOL.
- M equals the number of outputs driving TTL loads to VOH.

Accurate values for N and M are difficult to determine because they depend on the family type, on design details, and on the system I/O. The power can be divided into two components: static and active.

3.4.2 Static Power Component

The static power due to standby current is typically a small component of the overall power consumption. Standby power is calculated for commercial, worst-case conditions. The static power dissipation by TTL loads depends on the number of outputs driving, and on the DC load current. For instance, a 32-bit bus sinking 4mA at 0.33V will generate 42mW with all outputs driving LOW, and 140mW with all outputs driving HIGH. The actual dissipation will average somewhere in between, as I/Os switch states with time.

3.4.3 Active Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. Dynamic power consumption is frequency-dependent and is a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitances due to PC board traces and load device inputs. An additional component of the active power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

The power dissipated by a CMOS circuit can be expressed by the equation:

$$Power(\mu W) = C_{EQ} * VCCA2 * F(1)$$

EQ 2

where:

- C_{EQ} = Equivalent capacitance expressed in picofarads (pF)

- VCCA = Power supply in volts (V)
- F = Switching frequency in megahertz (MHz)

3.4.4 Equivalent Capacitance

Equivalent capacitance is calculated by measuring ICCactive at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

3.4.5 C_{EQ} Values for Microsemi MX FPGAs

Modules (C_{EQM})3.5

Input Buffers (C_{EQI})6.9

Output Buffers (C_{EQO})18.2

Routed Array Clock Buffer Loads (C_{EQCR})1.4

To calculate the active power dissipated from the complete design, the switching frequency of each part of the logic must be known. The equation below shows a piece-wise linear summation over all components.

$$\text{Power} = \text{VCCA}^2 \ {*}[(m \times C_{EQM} {*} f_m)_{modules} + (n {*} C_{EQI} {*} f_n)_{inputs} + (p {*} (C_{EQO} + C_L) {*} f_p)_{outputs} +$$
$$0.5 {*} (q_1 {*} C_{EQCR} {*} f_{q1})_{routed\_Clk1} + (r_{1*} f_{q1})_{routed\_Clk1} +$$
$$0.5 {*} (q_2 {*} C_{EQCR} {*} f_{q2})_{routed\_Clk2} + (r_{2*} f_{q2})_{routed\_Clk2} (2)]$$

EQ 3

where:

m = Number of logic modules switching at frequency f_m

n = Number of input buffers switching at frequency f_n

p = Number of output buffers switching at frequency f_p

q_1 = Number of clock loads on the first routed array clock

q_2 = Number of clock loads on the second routed array clock

r_1 = Fixed capacitance due to first routed array clock

r_2 = Fixed capacitance due to second routed array clock

C_{EQM} = Equivalent capacitance of logic modules in pF

C_{EQI} = Equivalent capacitance of input buffers in pF

C_{EQO} = Equivalent capacitance of output buffers in pF

C_{EQCR} = Equivalent capacitance of routed array clock in pF

C_L = Output load capacitance in pF

f_m = Average logic module switching rate in MHz

f_n = Average input buffer switching rate in MHz

f_p = Average output buffer switching rate in MHz

f_{q1} = Average first routed array clock rate in MHz

3.8.1 3.3 V LVTTL Electrical Specifications

Table 19 • **3.3V LVTTL Electrical Specifications**

		Commercial		Commercial -F		Industrial		Military		
Symbol	**Parameter**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
VOH[1]	IOH = –4 mA	2.15		2.15		2.4		2.4		V
VOL[1]	IOL = 6 mA		0.4		0.4		0.48		0.48	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH (40MX)		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
VIH (42MX)		2.0	VCCI + 0.3	2.0	VCCI + 0.3	2.0	VCCI + 0.3	2.0	VCCI + 0.3	V
IIL			–10		–10		–10		–10	µA
IIH			–10		–10		–10		–10	µA
Input Transition Time, T_R and T_F			500		500		500		500	ns
C_{IO} I/O Capacitance			10		10		10		10	pF
Standby Current, ICC[2]	A40MX02, A40MX04		3		25		10		25	mA
	A42MX09		5		25		25		25	mA
	A42MX16		6		25		25		25	mA
	A42MX24, A42MX36		15		25		25		25	mA
Low-Power Mode Standby Current	42MX devices only		0.5		ICC - 5.0		ICC - 5.0		ICC - 5.0	mA
IIO, I/O source sink current	Can be derived from the *IBIS model* (http://www.microsemi.com/soc/techdocs/models/ibis.html)									

1. Only one output tested at a time. VCC/VCCI = min.
2. All outputs unloaded. All inputs = VCC/VCCI or GND.

3.9 Mixed 5.0 V / 3.3 V Operating Conditions (for 42MX Devices Only)

Table 20 • **Absolute Maximum Ratings***

Symbol	Parameter	Limits	Units
VCCI	DC Supply Voltage for I/Os	–0.5 to +7.0	V
VCCA	DC Supply Voltage for Array	–0.5 to +7.0	V
VI	Input Voltage	–0.5 to VCCA +0.5	V
VO	Output Voltage	–0.5 to VCCI + 0.5	V
t_{STG}	Storage Temperature	–65 to +150	°C

Note: *Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. Exposure to absolute maximum rated conditions for extended periods may affect device

3.9.3 Output Drive Characteristics for 3.3 V PCI Signaling

Table 25 • **DC Specification (3.3 V PCI Signaling)[1]**

Symbol	Parameter	Condition	PCI Min.	PCI Max.	MX Min.	MX Max.	Units
VCCI	Supply Voltage for I/Os		3.0	3.6	3.0	3.6[2]	V
VIH	Input High Voltage		0.5	VCC + 0.5	0.5	VCCI + 0.3	V
VIL	Input Low Voltage		–0.5	0.8	–0.3	0.8	V
IIH	Input High Leakage Current	VIN = 2.7 V		70		10	µA
IIL	Input Leakage Current			–70		–10	µA
VOH	Output High Voltage	IOUT = –2 mA	0.9		3.3		V
VOL	Output Low Voltage	IOUT = 3 mA, 6 mA		0.1		0.1 VCCI	V
C_{IN}	Input Pin Capacitance			10		10	pF
C_{CLK}	CLK Pin Capacitance		5	12		10	pF
L_{PIN}	Pin Inductance			20		< 8 nH[3]	nH

1. PCI Local Bus Specification, Version 2.1, Section 4.2.2.1.
2. Maximum rating for VCCI –0.5 V to 7.0V.
3. Dependent upon the chosen package. PCI recommends QFP and BGA packaging to reduce pin inductance and capacitance.

Table 26 • **AC Specifications for (3.3 V PCI Signaling)***

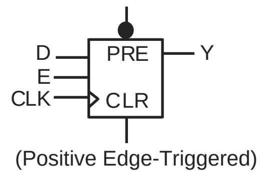
Symbol	Parameter	Condition	PCI Min.	PCI Max.	MX Min.	MX Max.	Units
ICL	Low Clamp Current	–5 < VIN ≤ –1	–25 + (VIN +1) /0.015		–60	–10	mA
Slew (r)	Output Rise Slew Rate	0.2 V to 0.6 V load	1	4	1.8	2.8	V/ns
Slew (f)	Output Fall Slew Rate	0.6 V to 0.2 V load	1	4	2.8	4.0	V/ns

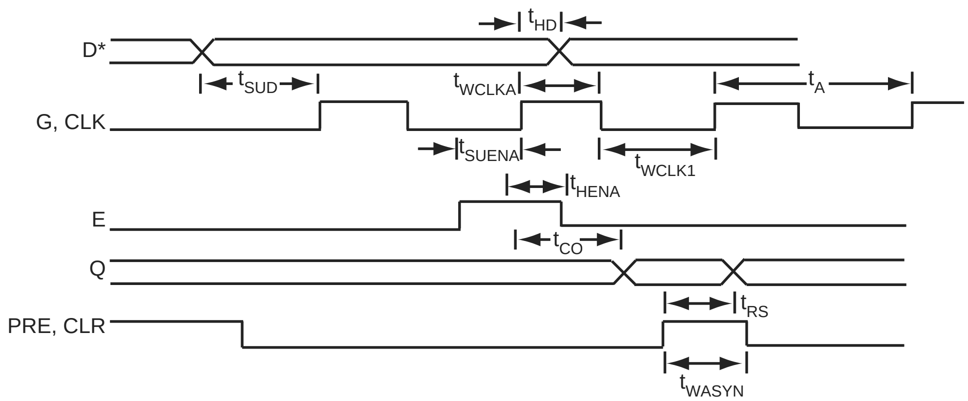
Note: *PCI Local Bus Specification, Version 2.1, Section 4.2.2.2.

3.10.2 Sequential Module Timing Characteristics

The following figure shows sequential module timing characteristics.

Figure 25 • **Flip-Flops and Latches**



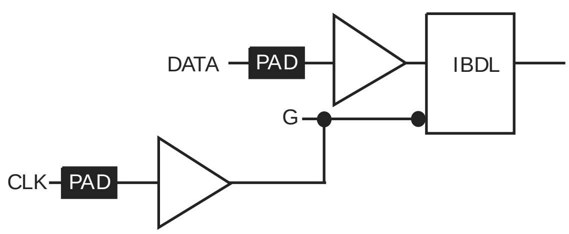


Note: *D represents all data functions involving A, B, and S for multiplexed flip-flops.

3.10.3 Sequential Timing Characteristics

The following figures show sequential timing characteristics.

Figure 26 • **Input Buffer Latches**



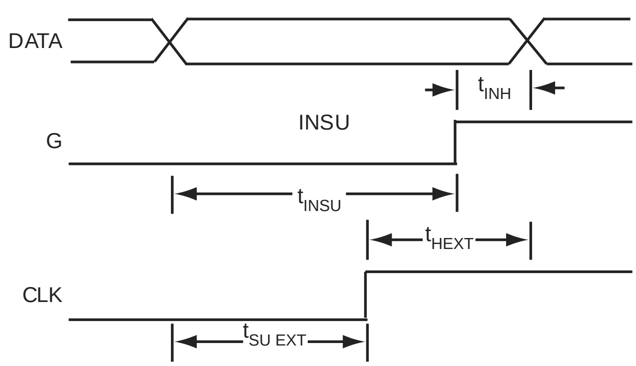
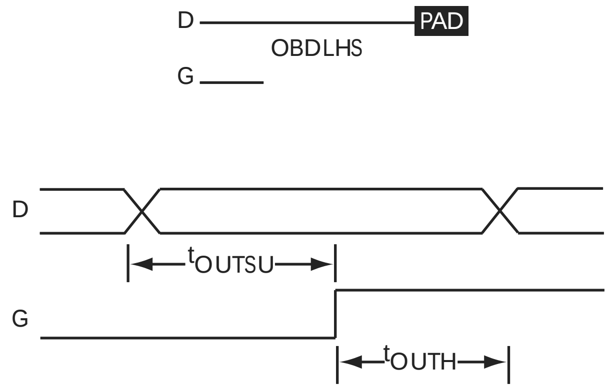


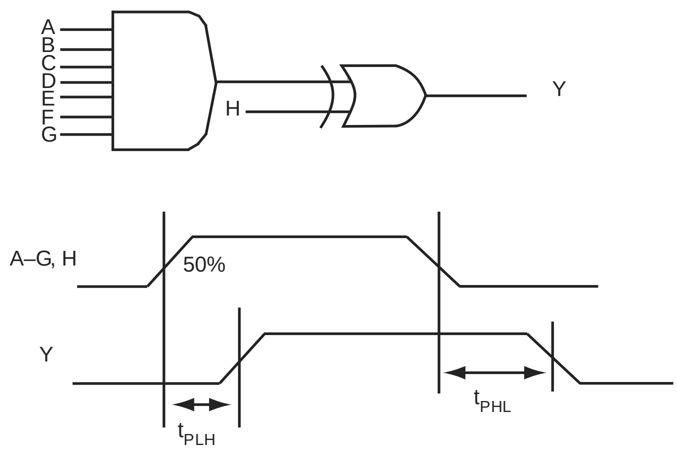
Figure 27 • **Output Buffer Latches**



3.10.4 Decode Module Timing

The following figure shows decode module timing.

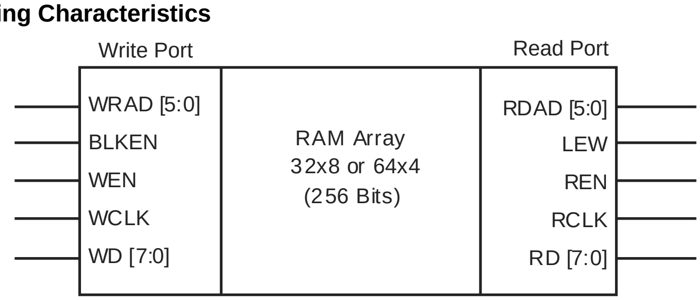
Figure 28 • **Decode Module Timing**



3.10.5 SRAM Timing Characteristics

The following figure shows SRAM timing characteristics.

Figure 29 • **SRAM Timing Characteristics**



3.10.6 Dual-Port SRAM Timing Waveforms

The following figures show dual-port SRAM timing waveforms.

approximately a 3 ns to a 6 ns delay, which is represented statistically in higher fanout (FO=8) routing delays in the data sheet specifications section, shown in Table 34, page 41.

3.11.3 Timing Derating

MX devices are manufactured with a CMOS process. Therefore, device performance varies according to temperature, voltage, and process changes. Minimum timing parameters reflect maximum operating voltage, minimum operating temperature and best-case processing. Maximum timing parameters reflect minimum operating voltage, maximum operating temperature and worst-case processing.

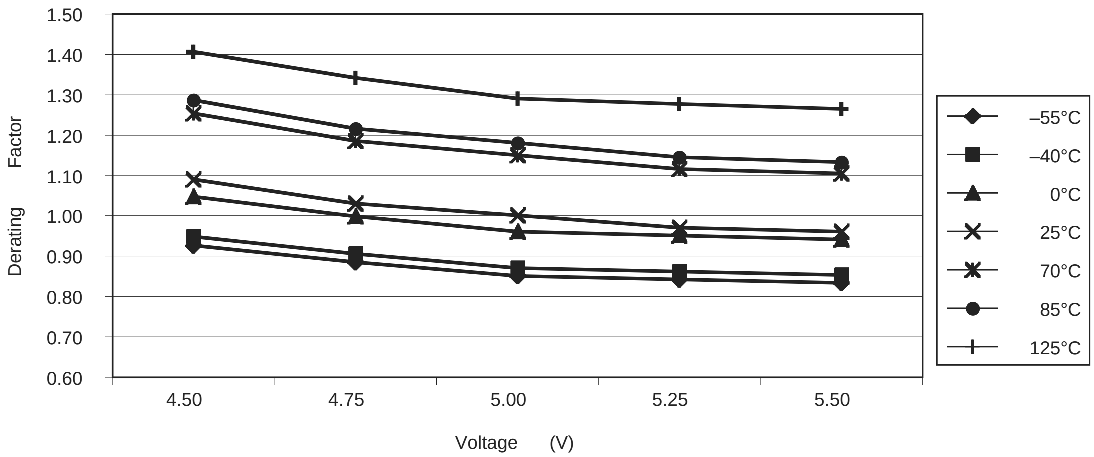
3.11.4 Temperature and Voltage Derating Factors

The following tables and figures show temperature and voltage derating factors for 40MX and 42MX FPGAs.

Table 28 • **42MX Temperature and Voltage Derating Factors (Normalized to T_J = 25°C, VCCA = 5.0 V)**

	Temperature						
42MX Voltage	**–55°C**	**–40°C**	**0°C**	**25°C**	**70°C**	**85°C**	**125°C**
4.50	0.93	0.95	1.05	1.09	1.25	1.29	1.41
4.75	0.88	0.90	1.00	1.03	1.18	1.22	1.34
5.00	0.85	0.87	0.96	1.00	1.15	1.18	1.29
5.25	0.84	0.86	0.95	0.97	1.12	1.14	1.28
5.50	0.83	0.85	0.94	0.96	1.10	1.13	1.26

Figure 34 • **42MX Junction Temperature and Voltage Derating Curves (Normalized to TJ = 25°C, VCCA = 5.0 V)**



Note: This derating factor applies to all routing and propagation delays

Table 29 • **40MX Temperature and Voltage Derating Factors(Normalized to TJ = 25°C, VCC = 5.0 V)**

	Temperature						
40MX Voltage	**–55°C**	**–40°C**	**0°C**	**25°C**	**70°C**	**85°C**	**125°C**
4.50	0.89	0.93	1.02	1.09	1.25	1.31	1.45
4.75	0.84	0.88	0.97	1.03	1.18	1.24	1.37
5.00	0.82	0.85	0.94	1.00	1.15	1.20	1.33
5.25	0.80	0.82	0.91	0.97	1.12	1.16	1.29
5.50	0.79	0.82	0.90	0.96	1.10	1.15	1.28

Table 37 • **A40MX04 Timing Characteristics (Nominal 3.3 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCC = 3.0 V, T_J = 70°C)**

Parameter / Description		–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
CMOS Output Module Timing[4]												
t_{DLH}	Data-to-Pad HIGH		5.5		6.4		7.2		8.5		11.9	ns
t_{DHL}	Data-to-Pad LOW		4.8		5.5		6.2		7.3		10.2	ns
t_{ENZH}	Enable Pad Z to HIGH		4.7		5.5		6.2		7.3		10.2	ns
t_{ENZL}	Enable Pad Z to LOW		6.8		7.9		8.9		10.5		14.7	ns
t_{ENHZ}	Enable Pad HIGH to Z		11.1		12.8		14.5		17.1		23.9	ns
t_{ENLZ}	Enable Pad LOW to Z		8.2		9.5		10.7		12.6		17.7	ns
d_{TLH}	Delta LOW to HIGH		0.05		0.05		0.06		0.07		0.10	ns/pF
d_{THL}	Delta HIGH to LOW		0.03		0.03		0.04		0.04		0.06	ns/pF

1. Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual performance.
2. Set-up times assume fanout of 3. Further testing information can be obtained from the Timer utility.
3. The hold time for the DFME1A macro may be greater than 0 ns. Use the Timer tool from the Designer software to check the hold time for this macro.
4. Delays based on 35 pF loading.

Table 38 • **A42MX09 Timing Characteristics (Nominal 5.0 V Operation) (Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)**

Parameter / Description		–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Logic Module Propagation Delays[1]												
t_{PD1}	Single Module		1.2		1.3		1.5		1.8		2.5	ns
t_{CO}	Sequential Clock-to-Q		1.3		1.4		1.6		1.9		2.7	ns
t_{GO}	Latch G-to-Q		1.2		1.4		1.6		1.8		2.6	ns
t_{RS}	Flip-Flop (Latch) Reset-to-Q		1.2		1.6		1.8		2.1		2.9	ns
Logic Module Predicted Routing Delays[2]												
t_{RD1}	FO = 1 Routing Delay		0.7		0.8		0.9		1.0		1.4	ns
t_{RD2}	FO = 2 Routing Delay		0.9		1.0		1.2		1.4		1.9	ns
t_{RD3}	FO = 3 Routing Delay		1.2		1.3		1.5		1.7		2.4	ns
t_{RD4}	FO = 4 Routing Delay		1.4		1.5		1.7		2.0		2.9	ns
t_{RD8}	FO = 8 Routing Delay		2.3		2.6		2.9		3.4		4.8	ns
Logic Module Sequential Timing[3, 4]												
t_{SUD}	Flip-Flop (Latch) Data Input Set-Up	0.3		0.4		0.4		0.5		0.7		ns
t_{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{SUENA}	Flip-Flop (Latch) Enable Set-Up	0.4		0.5		0.5		0.6		0.8		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	3.4		3.8		4.3		5.0		7.0		ns

Table 38 • **A42MX09 Timing Characteristics (Nominal 5.0 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)**

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
Input Module Propagation Delays													
t_{INYH}	Pad-to-Y HIGH			1.0		1.2		1.3		1.6		2.2	ns
t_{INYL}	Pad-to-Y LOW			0.8		0.9		1.0		1.2		1.7	ns
t_{INGH}	G to Y HIGH			1.3		1.4		1.6		1.9		2.7	ns
t_{INGL}	G to Y LOW			1.3		1.4		1.6		1.9		2.7	ns
Input Module Predicted Routing Delays[2]													
t_{IRD1}	FO = 1 Routing Delay			2.0		2.2		2.5		3.0		4.2	ns
t_{IRD2}	FO = 2 Routing Delay			2.3		2.5		2.9		3.4		4.7	ns
t_{IRD3}	FO = 3 Routing Delay			2.5		2.8		3.2		3.7		5.2	ns
t_{IRD4}	FO = 4 Routing Delay			2.8		3.1		3.5		4.1		5.7	ns
t_{IRD8}	FO = 8 Routing Delay			3.7		4.1		4.7		5.5		7.7	ns
Global Clock Network													
t_{CKH}	Input LOW to HIGH	FO = 32 FO = 256		2.4 2.7		2.7 3.0		3.0 3.4		3.6 4.0		5.0 5.5	ns ns
t_{CKL}	Input HIGH to LOW	FO = 32 FO = 256		3.5 3.9		3.9 4.3		4.4 4.9		5.2 5.7		7.3 8.0	ns ns
t_{PWH}	Minimum Pulse Width HIGH	FO = 32 FO = 256	1.2 1.3		1.4 1.5		1.5 1.7		1.8 2.0		2.5 2.7		ns ns
t_{PWL}	Minimum Pulse Width LOW	FO = 32 FO = 256	1.2 1.3		1.4 1.5		1.5 1.7		1.8 2.0		2.5 2.7		ns ns
t_{CKSW}	Maximum Skew	FO = 32 FO = 256		0.3 0.3		0.3 0.3		0.4 0.4		0.5 0.5		0.6 0.6	ns ns
t_{SUEXT}	Input Latch External Set-Up	FO = 32 FO = 256	0.0 0.0		0.0 0.0		0.0 0.0		0.0 0.0		0.0 0.0		ns ns
t_{HEXT}	Input Latch External Hold	FO = 32 FO = 256	2.3 2.2		2.6 2.4		3.0 3.3		3.5 3.9		4.9 5.5		ns ns
t_P	Minimum Period	FO = 32 FO = 256	3.4 3.7		3.7 4.1		4.0 4.5		4.7 5.2		7.8 8.6		ns ns
f_{MAX}	Maximum Frequency	FO = 32 FO = 256		296 268		269 244		247 224		215 195		129 117	MHz MHz

Table 39 • A42MX09 Timing Characteristics (Nominal 3.3 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

Parameter / Description		–3 Speed Min.	–3 Speed Max.	–2 Speed Min.	–2 Speed Max.	–1 Speed Min.	–1 Speed Max.	Std Speed Min.	Std Speed Max.	–F Speed Min.	–F Speed Max.	Units
CMOS Output Module Timing[5]												
t_{DLH}	Data-to-Pad HIGH		3.4		3.8		5.5		6.4		9.0	ns
t_{DHL}	Data-to-Pad LOW		4.1		4.5		4.2		5.0		7.0	ns
t_{ENZH}	Enable Pad Z to HIGH		3.7		4.1		4.6		5.5		7.6	ns
t_{ENZL}	Enable Pad Z to LOW		4.1		4.5		5.1		6.1		8.5	ns
t_{ENHZ}	Enable Pad HIGH to Z		6.9		7.6		8.6		10.2		14.2	ns
t_{ENLZ}	Enable Pad LOW to Z		7.5		8.3		9.4		11.1		15.5	ns
t_{GLH}	G-to-Pad HIGH		5.8		6.5		7.3		8.6		12.0	ns
t_{GHL}	G-to-Pad LOW		5.8		6.5		7.3		8.6		12.0	ns
t_{LSU}	I/O Latch Set-Up	0.7		0.8		0.9		1.0		1.4		ns
t_{LH}	I/O Latch Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{LCO}	I/O Latch Clock-to-Out (Pad-to-Pad), 64 Clock Loading		8.7		9.7		10.9		12.9		18.0	ns
t_{ACO}	Array Clock-to-Out (Pad-to-Pad), 64 Clock Loading		12.2		13.5		15.4		18.1		25.3	ns
d_{TLH}	Capacity Loading, LOW to HIGH		0.04		0.04		0.05		0.06		0.08	ns/pF
d_{THL}	Capacity Loading, HIGH to LOW		0.05		0.05		0.06		0.07		0.10	ns/pF

1. *For dual-module macros, use t_{PD1} + t_{RD1} + t_{PDn}, t_{CO} + t_{RD1} + t_{PDn}, or t_{PD1} + t_{RD1} + t_{SUD}, whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual performance.*
3. *Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the Timer utility.*
4. *Set-up and hold timing parameters for the input buffer latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.*
5. *Delays based on 35 pF loading.*

Table 40 • A42MX16 Timing Characteristics (Nominal 5.0 V Operation) (Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)

Parameter / Description		–3 Speed Min.	–3 Speed Max.	–2 Speed Min.	–2 Speed Max.	–1 Speed Min.	–1 Speed Max.	Std Speed Min.	Std Speed Max.	–F Speed Min.	–F Speed Max.	Units
Logic Module Propagation Delays[1]												
t_{PD1}	Single Module		1.4		1.5		1.7		2.0		2.8	ns
t_{CO}	Sequential Clock-to-Q		1.4		1.6		1.8		2.1		3.0	ns
t_{GO}	Latch G-to-Q		1.4		1.5		1.7		2.0		2.8	ns
t_{RS}	Flip-Flop (Latch) Reset-to-Q		1.6		1.7		2.0		2.3		3.3	ns
Logic Module Predicted Routing Delays[2]												
t_{RD1}	FO = 1 Routing Delay		0.8		0.9		1.0		1.2		1.6	ns
t_{RD2}	FO = 2 Routing Delay		1.0		1.2		1.3		1.5		2.1	ns

Table 42 • **A42MX24 Timing Characteristics (Nominal 5.0 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)**

Parameter / Description		–3 Speed Min.	–3 Speed Max.	–2 Speed Min.	–2 Speed Max.	–1 Speed Min.	–1 Speed Max.	Std Speed Min.	Std Speed Max.	–F Speed Min.	–F Speed Max.	Units
TTL Output Module Timing[5]												
t_{DLH}	Data-to-Pad HIGH		2.4		2.7		3.1		3.6		5.1	ns
t_{DHL}	Data-to-Pad LOW		2.8		3.2		3.6		4.2		5.9	ns
t_{ENZH}	Enable Pad Z to HIGH		2.5		2.8		3.2		3.8		5.3	ns
t_{ENZL}	Enable Pad Z to LOW		2.8		3.1		3.5		4.2		5.9	ns
t_{ENHZ}	Enable Pad HIGH to Z		5.2		5.7		6.5		7.6		10.7	ns
t_{ENLZ}	Enable Pad LOW to Z		4.8		5.3		6.0		7.1		9.9	ns
t_{GLH}	G-to-Pad HIGH		2.9		3.2		3.6		4.3		6.0	ns
t_{GHL}	G-to-Pad LOW		2.9		3.2		3.6		4.3		6.0	ns
t_{LSU}	I/O Latch Output Set-Up	0.5		0.5		0.6		0.7		1.0		ns
t_{LH}	I/O Latch Output Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{LCO}	I/O Latch Clock-to-Out (Pad-to-Pad) 32 I/O		5.6		6.1		6.9		8.1		11.4	ns
t_{ACO}	Array Latch Clock-to-Out (Pad-to-Pad) 32 I/O		10.6		11.8		13.4		15.7		22.0	ns
d_{TLH}	Capacitive Loading, LOW to HIGH		0.04		0.04		0.04		0.05		0.07	ns/pF
d_{THL}	Capacitive Loading, HIGH to LOW		0.03		0.03		0.03		0.04		0.06	ns/pF

Table 44 • **A42MX36 Timing Characteristics (Nominal 5.0 V Operation)(Worst-Case Commercial Conditions, VCCA = 4.75 V, T_J = 70°C)**

Parameter / Description			–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
			Min.	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
t_{SUEXT}	Input Latch External Set-Up	FO = 32 FO = 635	0.0 0.0		0.0 0.0		0.0 0.0		0.0 0.0		0.0 0.0		ns ns
t_{HEXT}	Input Latch External Hold	FO = 32 FO = 635	2.8 3.3		3.2 3.7		3.6 4.2		4.2 4.9		5.9 6.9		ns ns
t_P	Minimum Period ($1/f_{MAX}$)	FO = 32 FO = 635	5.5 6.0		6.1 6.6		6.6 7.2		7.6 8.3		12.7 13.8		ns ns
f_{MAX}	Maximum Datapath Frequency	FO = 32 FO = 635		180 166		164 151		151 139		131 121		79 73	MHz MHz
TTL Output Module Timing[5]													
t_{DLH}	Data-to-Pad HIGH			2.6		2.8		3.2		3.8		5.3	ns
t_{DHL}	Data-to-Pad LOW			3.0		3.3		3.7		4.4		6.2	ns
t_{ENZH}	Enable Pad Z to HIGH			2.7		3.0		3.3		3.9		5.5	ns
t_{ENZL}	Enable Pad Z to LOW			3.0		3.3		3.7		4.3		6.1	ns
t_{ENHZ}	Enable Pad HIGH to Z			5.3		5.8		6.6		7.8		10.9	ns

Table 45 • A42MX36 Timing Characteristics (Nominal 3.3 V Operation) *(continued)*(Worst-Case Commercial Conditions, VCCA = 3.0 V, T_J = 70°C)

Parameter / Description		–3 Speed		–2 Speed		–1 Speed		Std Speed		–F Speed		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Units
t_{RD5}	FO = 8 Routing Delay		4.6		5.2		5.8		6.9		9.6	ns
t_{RDD}	Decode-to-Output Routing Delay		0.5		0.5		0.6		0.7		1.0	ns
Logic Module Sequential Timing[3, 4]												
t_{CO}	Flip-Flop Clock-to-Output		1.8		2.0		2.3		2.7		3.7	ns
t_{GO}	Latch Gate-to-Output		1.8		2.0		2.3		2.7		3.7	ns
t_{SUD}	Flip-Flop (Latch) Set-Up Time	0.4		0.5		0.6		0.7		0.9		ns
t_{HD}	Flip-Flop (Latch) Hold Time	0.0		0.0		0.0		0.0		0.0		ns
t_{RO}	Flip-Flop (Latch) Reset-to-Output		2.2		2.4		2.7		3.2		4.5	ns
t_{SUENA}	Flip-Flop (Latch) Enable Set-Up	1.0		1.1		1.2		1.4		2.0		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	4.6		5.2		5.8		6.9		9.6		ns
t_{WASYN}	Flip-Flop (Latch) Asynchronous Pulse Width	6.1		6.8		7.7		9.0		12.6		ns
Synchronous SRAM Operations												
t_{RC}	Read Cycle Time	9.5		10.5		11.9		14.0		19.6		ns
t_{WC}	Write Cycle Time	9.5		10.5		11.9		14.0		19.6		ns
t_{RCKHL}	Clock HIGH/LOW Time	4.8		5.3		6.0		7.0		9.8		ns
t_{RCO}	Data Valid After Clock HIGH/LOW		4.8		5.3		6.0		7.0		9.8	ns
t_{ADSU}	Address/Data Set-Up Time	2.3		2.5		2.8		3.4		4.8		ns

Table 57 • **TQ176**

TQ176			
Pin Number	**A42MX09 Function**	**A42MX16 Function**	**A42MX24 Function**
121	NC	NC	I/O
122	I/O	I/O	I/O
123	I/O	I/O	I/O
124	NC	I/O	I/O
125	NC	I/O	I/O
126	NC	NC	I/O
127	I/O	I/O	I/O
128	I/O	I/O	I/O
129	I/O	I/O	I/O
130	I/O	I/O	I/O
131	I/O	I/O	I/O
132	I/O	I/O	I/O
133	GND	GND	GND
134	I/O	I/O	I/O
135	SDI, I/O	SDI, I/O	SDI, I/O
136	NC	I/O	I/O
137	I/O	I/O	WD, I/O
138	I/O	I/O	WD, I/O
139	I/O	I/O	I/O
140	NC	VCCI	VCCI
141	I/O	I/O	I/O
142	I/O	I/O	I/O
143	NC	I/O	I/O
144	NC	I/O	WD, I/O
145	NC	NC	WD, I/O
146	I/O	I/O	I/O
147	NC	I/O	I/O
148	I/O	I/O	I/O
149	I/O	I/O	I/O
150	I/O	I/O	WD, I/O
151	NC	I/O	WD, I/O
152	PRA, I/O	PRA, I/O	PRA, I/O
153	I/O	I/O	I/O
154	CLKA, I/O	CLKA, I/O	CLKA, I/O
155	VCCA	VCCA	VCCA
156	GND	GND	GND
157	I/O	I/O	I/O

Table 59 • **CQ256**

CQ256	
Pin Number	**A42MX36 Function**
59	I/O
60	VCCA
61	GND
62	GND
63	NC
64	NC
65	NC
66	I/O
67	SDO, TDO, I/O
68	I/O
69	WD, I/O
70	WD, I/O
71	I/O
72	VCCI
73	I/O
74	I/O
75	I/O
76	WD, I/O
77	GND
78	WD, I/O
79	I/O
80	QCLKB, I/O
81	I/O
82	I/O
83	I/O
84	I/O
85	I/O
86	I/O
87	WD, I/O
88	WD, I/O
89	I/O
90	I/O
91	I/O
92	I/O
93	I/O
94	I/O
95	VCCI

Table 59 • **CQ256**

CQ256	
Pin Number	**A42MX36 Function**
170	VCCA
171	I/O
172	I/O
173	I/O
174	I/O
175	I/O
176	I/O
177	I/O
178	I/O
179	I/O
180	GND
181	I/O
182	I/O
183	I/O
184	I/O
185	I/O
186	I/O
187	I/O
188	MODE
189	VCCA
190	GND
191	NC
192	NC
193	NC
194	I/O
195	DCLK, I/O
196	I/O
197	I/O
198	I/O
199	WD, I/O
200	WD, I/O
201	VCCI
202	I/O
203	I/O
204	I/O
205	I/O
206	GND

Table 60 • **BG272**

BG272	
Pin Number	**A42MX36 Function**
V16	I/O
V17	I/O
V18	SDO, TDO, I/O
V19	I/O
V20	I/O
W1	GND
W2	GND
W3	I/O
W4	TMS, I/O
W5	I/O
W6	I/O
W7	I/O
W8	WD, I/O
W9	WD, I/O
W10	I/O
W11	I/O
W12	I/O
W13	WD, I/O
W14	I/O
W15	I/O
W16	WD, I/O
W17	I/O
W18	WD, I/O
W19	GND
W20	GND
Y1	GND
Y2	GND
Y3	I/O
Y4	TDI, I/O
Y5	WD, I/O
Y6	I/O
Y7	QCLKA, I/O
Y8	I/O
Y9	I/O
Y10	I/O
Y11	I/O
Y12	I/O

Figure 53 • **CQ172**

Table 62 • **CQ172**

CQ172	
Pin Number	**A42MX16 Function**
1	MODE
2	I/O
3	I/O
4	I/O
5	I/O
6	I/O
7	GND
8	I/O
9	I/O
10	I/O
11	I/O
12	VCC
13	I/O
14	I/O
15	I/O
16	I/O
17	GND
18	I/O
19	I/O
20	I/O

Table 62 • **CQ172**

99	I/O
100	I/O
101	I/O
102	I/O
103	GND
104	I/O
105	I/O
106	VKS
107	VPP
108	GND
109	VCCI
110	VSV
111	I/O
112	I/O
113	VCC
114	I/O
115	I/O
116	I/O
117	I/O
118	GND
119	I/O
120	I/O
121	I/O
122	I/O
123	GNDI
124	I/O
125	I/O
126	I/O
127	I/O
128	I/O
129	I/O
130	I/O
131	SDI
132	I/O
133	I/O
134	I/O
135	I/O
136	VCCI
137	I/O